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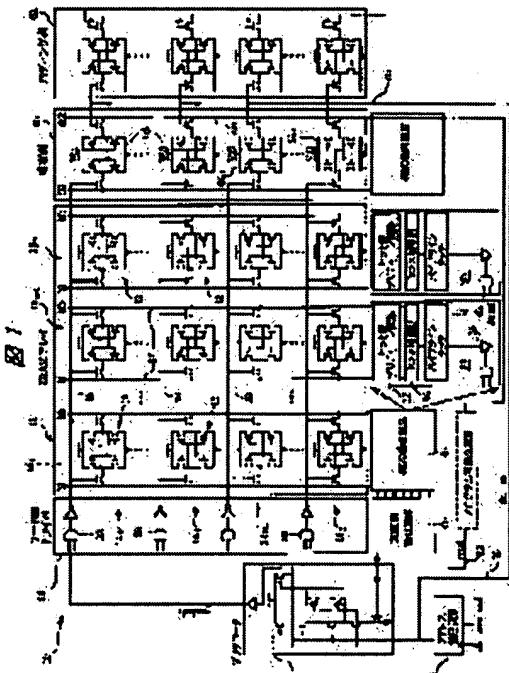
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(54) STATIC RANDOM ACCESS MEMORY OF CMOS, MEMORY CIRCUIT, AND METHOD FOR GENERATING SENSE-ENABLE SIGNAL

(57)Abstract:

PROBLEM TO BE SOLVED: To provide a technology by which a signal is supplied by using a self-measuring method and a sense amplifier is turned on, and multi-memory cells in a duplication column are made approximately the same capacitance as a reference bit line.

SOLUTION: A CMOS memory array includes many bit cells 12 arranged in a SRAM array 11 of N rows×M columns, and has a duplication columns 60 of the bit cell 12 utilized for self-measuring. The bit cells 12 of the prescribed numbers are accessed by receiving addresses, and a reset signal utilized for enabling a sense amplifier 34 sampling bit lines of the SRAM array 11 is generated.



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